

DESCRIPTION

174S-04F is a design which includes ESD rated diode arrays to protect high-speed data interfaces. The 174S-04F has been specifically designed to protect sensitive components which are connected to data and transmission lines from over-voltage caused by Electrostatic Discharging (ESD), Electrical Fast Transients (EFT), Lightning, and Cable Discharge Event (CDE).

174S-04F is a unique design which includes ESD rated, ultra-low capacitance steering diodes and a unique design of clamping cell which is an equivalent TVS diode in a single package. During transient conditions, the steering diodes direct the transient to either the internal ESD line or to ground line. The internal unique design of clamping cell prevents over-voltage on the internal ESD line and on the I/O line, which is protecting any downstream components.

174S-04F may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (\pm 15kV air, \pm 8kV contact discharge).

174S-04F is available in a DFN10 package.

ORDERING INFORMATION

Package Type	Part Number	
DFN10	174S-04F	
Note	SPQ: 3,000pcs/Reel	
AiT provides all RoHS Compliant Products		

FEATURES

- ESD protection for super speed differential signaling (above 10Gb/s) channels
- Protects four I/O lines
- Provide transient protection for each line to
 IEC 61000-4-2 (ESD) ±15kV (air), ±12kV (contact)
 IEC 61000-4-4 (EFT) 30A (5/50ns)
 IEC 61000-4-5 (Lightning) 4A (8/20us)
- For low operating voltage of 1.5V and below
- Ultra-low capacitance: 0.29pF typical
- Fast turn-on and ultra-low clamping voltage
- Array of ESD rated diodes with internal equivalent TVS (Transient Voltage Suppression) diode
- Solid-state silicon-avalanche and active circuit triggering technology
- Green part
- Available in a DFN10 package.

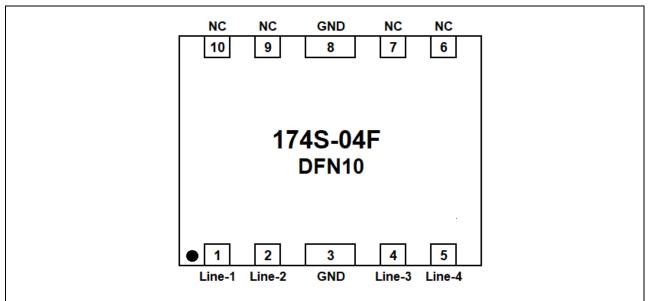
APPLICATION

- USB3.1 and USB3.0 interfaces
- Thunderbolt interface
- DisplayPort interface
- SATA and eSATA interface
- V-By-One interface
- Consumer electronics

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PIN DESCRIPTION



Top View

Pin#	Symbol	Function
1	Line-1	ESD-Protected Channel
2	Line-2	ESD-Protected Channel
3	GND	Ground
4	Line-3	ESD-Protected Channel
5	Line-4	ESD-Protected Channel
6	NC	No Connection
7	NC	No Connection
8	GND	Ground
9	NC	No Connection
10	NC	No Connection

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ABSOLUTE MAXIMUM RATINGS

T_A= 25°C, unless otherwise specified

- X = 0 0, amount of the contract of the contr	
IPP, Peak Pulse Current (tp =8/20µs)	4A
V _{DC} , Operating Voltage (I/O pin-GND)	1.65V
V _{ESD-1} , ESD per IEC 61000-4-2 (Air)	±15kV
V _{ESD-2} , ESD per IEC 61000-4-2 (Contact)	±12kV
T _{SOL} , Lead Soldering Temperature	260°C (10 sec.)
T _{OP} , Operating Temperature	-55°C ~ +125°C
T _{STO} , Storage Temperature	-55°C ~ +150°C

Stress beyond above listed "Absolute Maximum Ratings" may lead permanent damage to the device. These are stress ratings only and operations of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $T_A = 25$ °C, unless otherwise noted

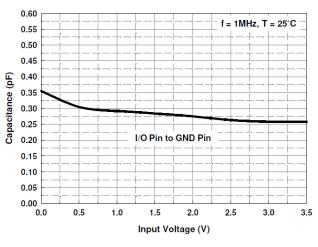
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Reverse Stand-Off Voltage	V _{RWM}	Pin-1,-2,-4,-5 to pin-3,-8, T=25°C.	-	-	1.5	V
Channel Leakage Current	I _{CH-Leak}	$V_{Pin-1,-2,-4,-5} = 1.5V, V_{Pin-3,-8} = 0V,$	-	-	1	μA
		T=25°C.				
Reverse Breakdown Voltage	V _{BV}	I _{BV} = 1mA, T=25°C, Pin-1,-2,-4,-5	5	-	8	V
		to pin-3,-8.				
Forward Voltage	VF	I _F = 15mA, T=25°C, pin-3,-8 to	-	0.9	1.1	V
		pin-1,-2,-4,-5.				
ESD Clamping VoltageNOTE1	V _{CL-ESD}	IEC 61000-4-2 +8kV (I _{TLP} = 16A),	-	4.3	-	V
		Contact mode, T=25°C, any I/O pin				
		to GND.				
ESD Dynamic		IEC 61000-4-2, 0~+8kV, T=25°C,	-	0.19	-	Ω
Turn-on Resistance	R _{dynamic}	Contact mode, any I/O pin to GND.				
Channel Input Capacitance	Cin	$V_{pin-3,-8} = 0V$, $V_{IN} = 1.0V$, $f = 1MHz$,	-	0.29	0.34	pF
		T=25°C, any I/O pin to GND.				
Channel to Channel Input		$V_{pin-3,-8} = 0V$, $V_{IN} = 1.0V$, $f = 1MHz$,	-	0.05	0.1	pF
Capacitance	Ccross	T=25°C, between I/O pins.				

NOTE1: ESD Clamping Voltage was measured by Transmission Line Pulsing (TLP) System. TLP conditions: Z_0 = 50 Ω , t_p = 100ns, t_r = 1ns.

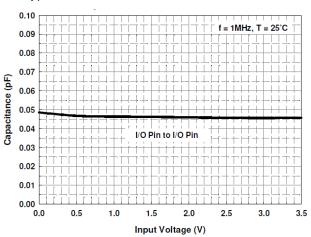
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TYPICAL CHARACTERISTICS

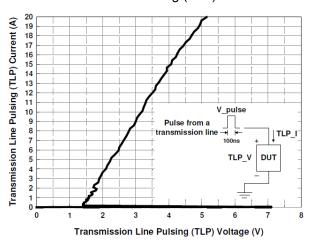
1. Typical Variation of CIN vs. VIN



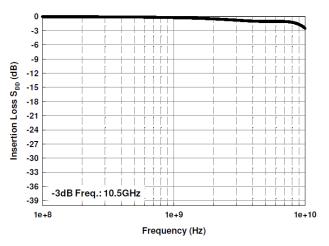
2. Typical Variation of C_{I/O-to-I/O} vs. V_{IN}



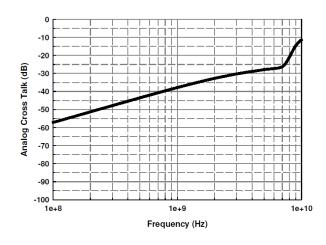
3. Transmission Line Pulsing (TLP) Measurement



4. Insertion Loss SDD

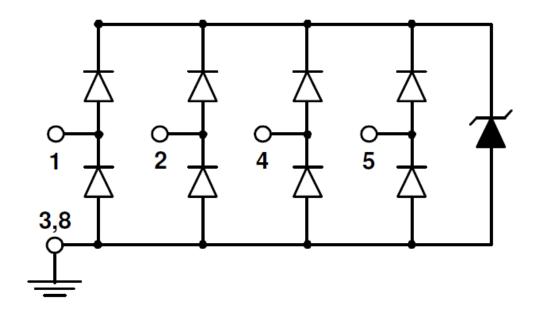


5. Analog Cross Talk



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CIRCUIT DIAGRAM



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APPLICATION INFORMATION

The 174S-04F is designed to protect four data lines from transient over-voltage (such as ESD stress pulse). The device connection of 174S-04F is shown in the Fig. 1. In Fig. 1, the four protected data lines are connected to the ESD protection pins (pin1, pin2, pin4, and pin5) of 174S-04F. The ground pins (pin3 and pin8) of 174S-04F are the negative reference pins.

These pins should be directly connected to the GND rail of PCB (Printed Circuit Board). To get minimum parasitic inductance, the path length should be kept as short as possible.

174S-04F can provide ESD protection for 4 I/O signal lines simultaneously. If the number of I/O signal lines is less than 4, the unused I/O pins can be simply left as NC pins.

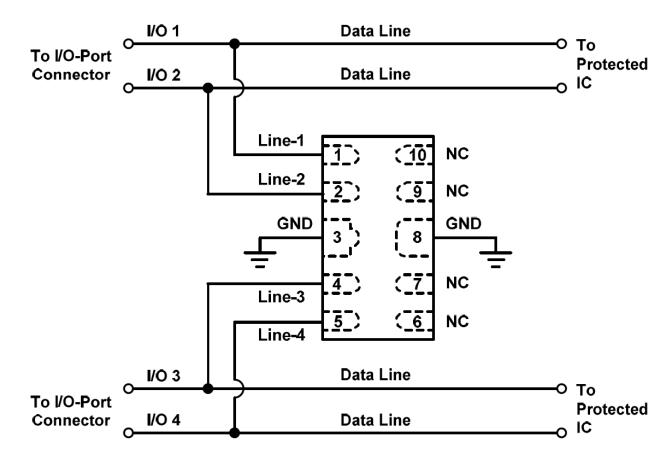
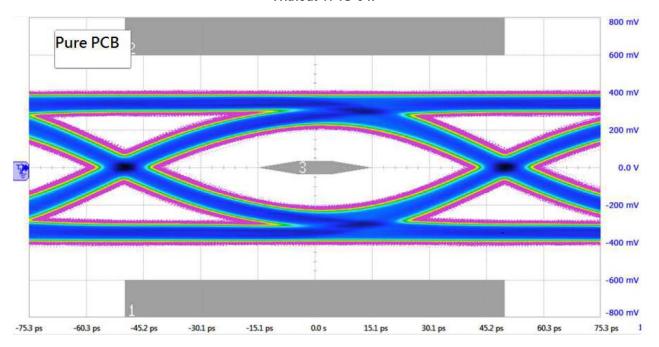


Fig. 1 Data lines connection of 174S-04F.

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Fig. 2 shows the USB3.1 (10 Gb/s) eye diagrams with and without 174S-04F. Due to the ultra-low capacitance, 174S-04F can be used for USB3.1 application.

Without 174S-04F



With 174S-04F

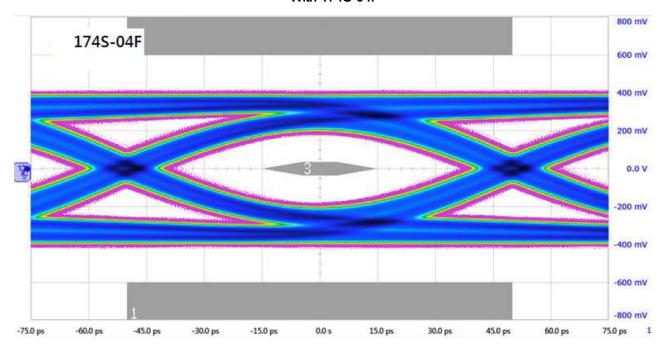


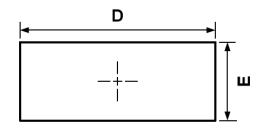
Fig. 2 USB3.1 (10Gb/s) eye diagrams with and without 174S-04F.

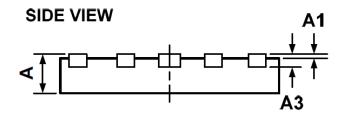
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PACKAGE INFORMATION

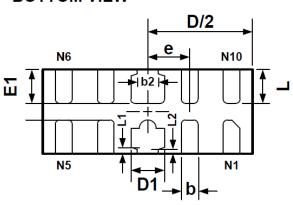
Dimension in DFN10 (Unit: mm)

TOP VIEW





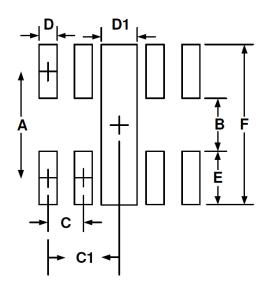
BOTTOM VIEW



Symbol	Min	Max		
А	0.400	0.550		
A1	-	0.050		
A3	0.152REF			
D	2.450	2.550		
E	0.950	1.050		
D1	0.350	0.450		
E1	0.350	0.450		
b	0.150	0.250		
е	0.500 BSC			
L1	0.075 REF			
L2	0.050 REF			
b2	0.200	0.300		
L	0.350	0.450		

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LAND LAYOUT



Index	Millimeter Inches	
Α	0.875	0.034
В	0.20	0.008
С	0.50	0.02
C1	1.00	0.039
D	0.25	0.01
D1	0.4	0.016
E	0.675	0.027
F	1.55	0.061

Notes: This LAND LAYOUT is for reference purposes only. Please consult your manufacturing partners to ensure your company's PCB design guidelines are met.

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